

TDS:EMIC

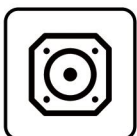
拓 電 半 導 體

自主封測 品質把控 售後保障

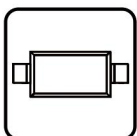
WEB | WWW.TDSEMIC.COM



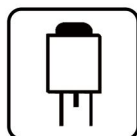
電源管理



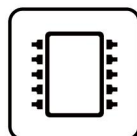
顯示驅動



二三極管



LDO穩壓器



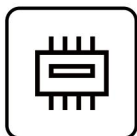
觸摸芯片



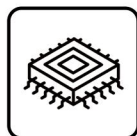
MOS管



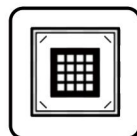
運算放大器



存儲芯片



MCU



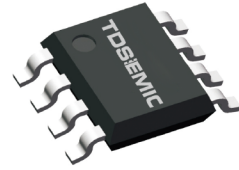
串口通信

AO4407-TD

產品規格說明書

Description

The AO4407 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.



SOP-8

General Features

$V_{DS} = -30V$ $I_D = -12A$

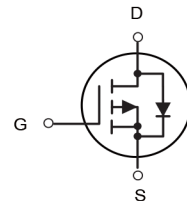
$R_{DS(ON)} < 15m\Omega @ V_{GS}=10V$

Application

Battery protection

Load switch

Uninterruptible power supply



P-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AO4407	SOP-8	4407 XXXX	3000

Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	+20	V
$I_D @ T_A=25^\circ C$	Drain Current ³ , $V_{GS} @ 10V$	-12	A
$I_D @ T_A=70^\circ C$	Drain Current ³ , $V_{GS} @ 10V$	-9.1	A
I_{DM}	Pulsed Drain Current ¹	-40	A
$P_D @ T_A=25^\circ C$	Total Power Dissipation	2.5	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C
R_{thj-a}	Maximum Thermal Resistance, Junction-ambient ³	50	°C/W

Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-30	-	-	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-10V, I _D =-10A	-	9.5	15	mΩ
		V _{GS} =-4.5V, I _D =-6A	-	15	25	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250uA	-1	-	-2.5	V
g _{fs}	Forward Transconductance	V _{DS} =-10V, I _D =-10A	-	22	-	S
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-24V, V _{GS} =0V	-	-	-10	uA
I _{GSS}	Gate-Source Leakage	V _{GS} =+20V, V _{DS} =0V	-	-	±100	nA
Q _g	Total Gate Charge	I _D =-6A	-	28	45	nC
Q _{gs}	Gate-Source Charge	V _{DS} =-15V	-	7	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =-4.5V	-	11	-	nC
t _{d(on)}	Turn-on Delay Time	V _{DS} =-15V	-	13	-	ns
t _r	Rise Time	I _D =-1A	-	10	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =3.3Ω	-	80	-	ns
t _f	Fall Time	V _{GS} =-10V	-	37	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V V _{DS} =-	-	2940	4700	pF
C _{oss}	Output Capacitance	15V f=1.0MHz	-	290	-	pF
C _{rss}	Reverse Transfer Capacitance		-	210	-	pF
R _g	Gate Resistance	f=1.0MHz	-	6.2	12.4	Ω
V _{SD}	Forward On Voltage ²	I _S =-2.1A, V _{GS} =0V	-	-	-1.2	V
t _{rr}	Reverse Recovery Time	I _S =-10A, V _{GS} =0V, dI/dt=100A/μs	-	19	-	ns
Q _{rr}	Reverse Recovery Charge		-	6	-	nC

Notes:

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse test
- 3.Surface mounted on 1 in² copper pad of FR4 board, t ≤ 10s ; 125 °C/W when mounted on Min. copper pad.

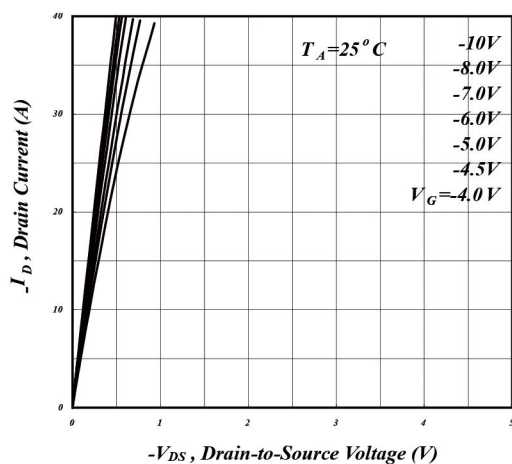


Fig 1. Typical Output Characteristics

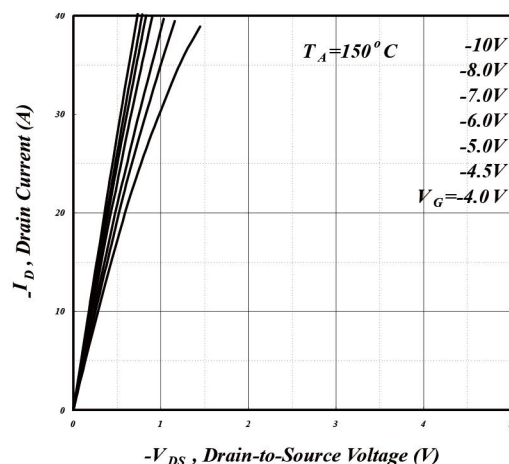


Fig 2. Typical Output Characteristics

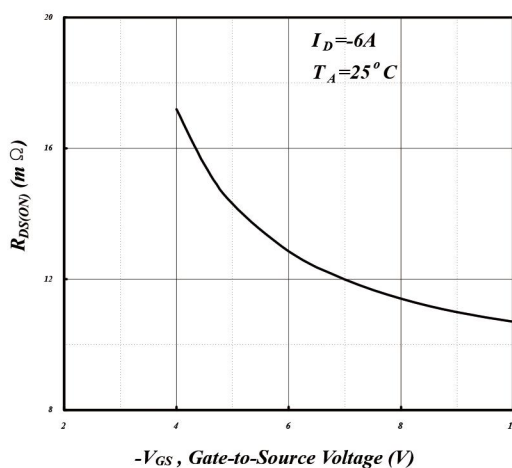


Fig 3. On-Resistance v.s. Gate Voltage

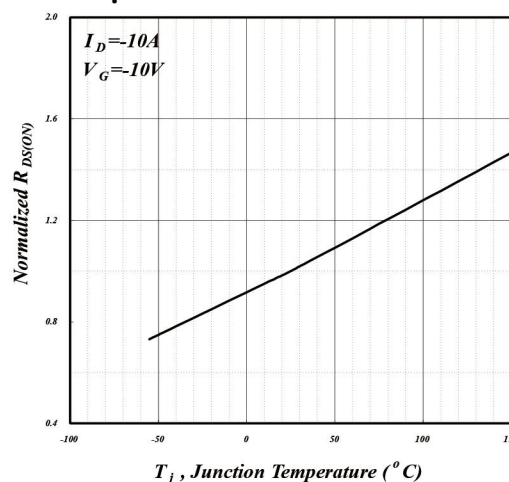
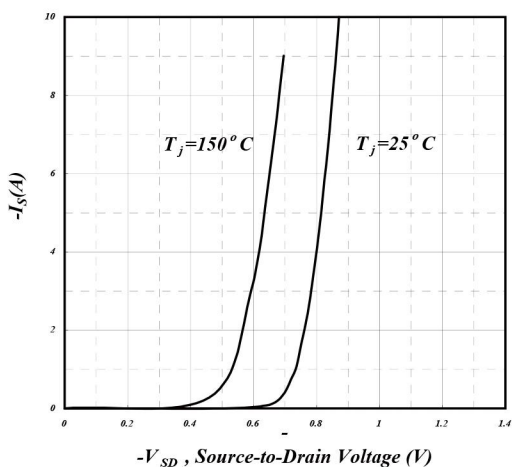


Fig 4. Normalized On-Resistance v.s. Junction Temperature



Reverse Diode

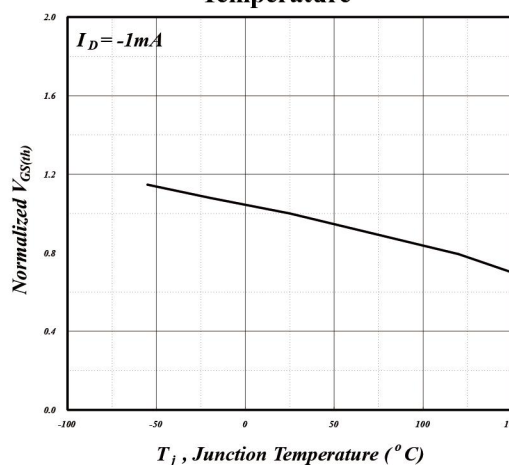


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

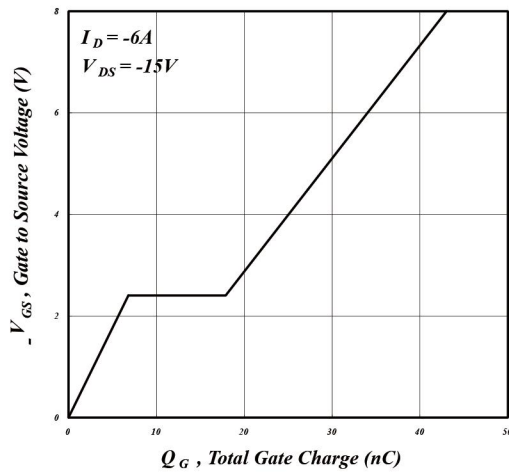


Fig 7. Gate Charge Characteristics

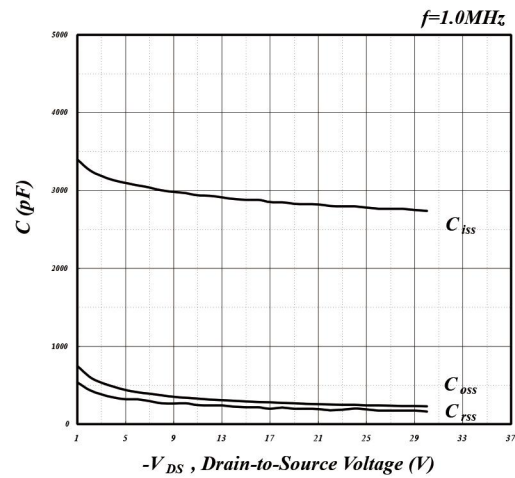


Fig 8. Typical Capacitance Characteristics

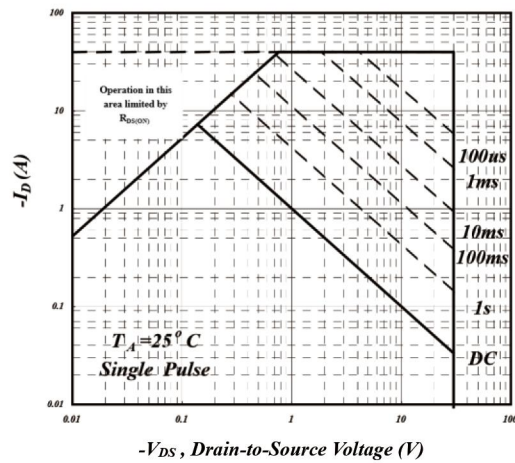


Fig 9. Maximum Safe Operating Area

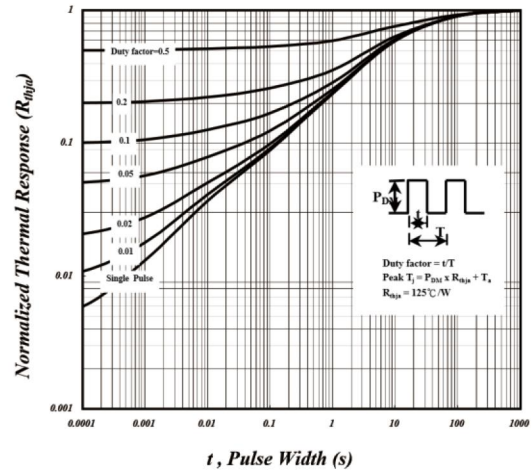


Fig 10. Effective Transient Thermal Impedance

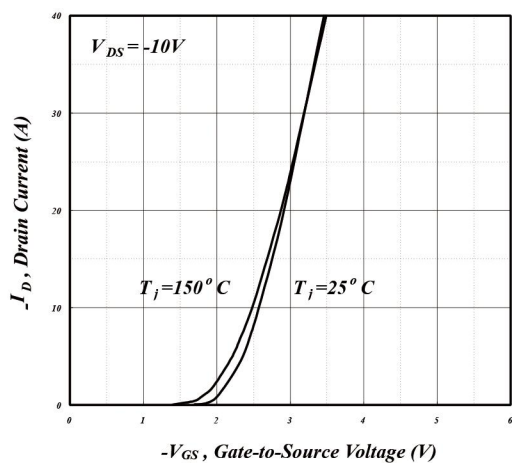


Fig 11. Transfer Characteristics

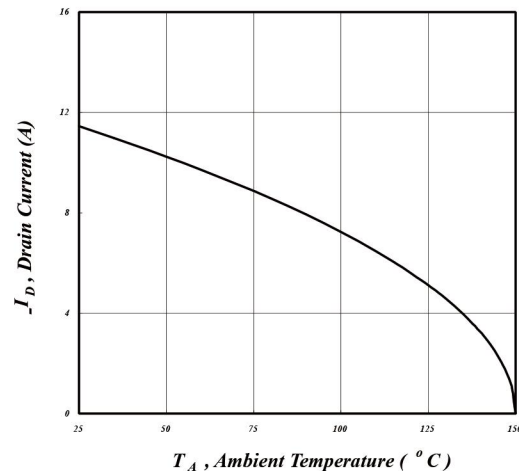


Fig 12. Drain Current v.s. Ambient Temperature

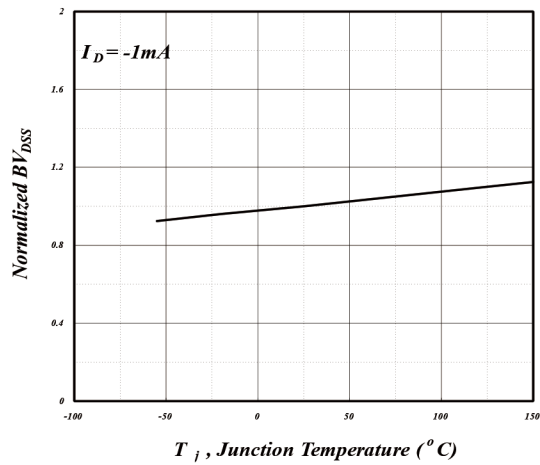


Fig 13. Normalized BV_{DSS} v.s. Junction Temperature

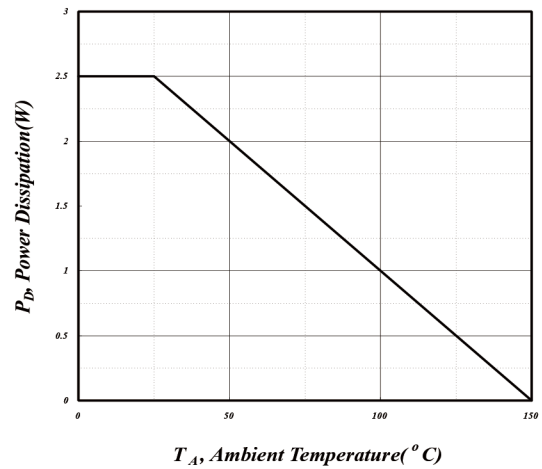


Fig 14. Total Power Dissipation

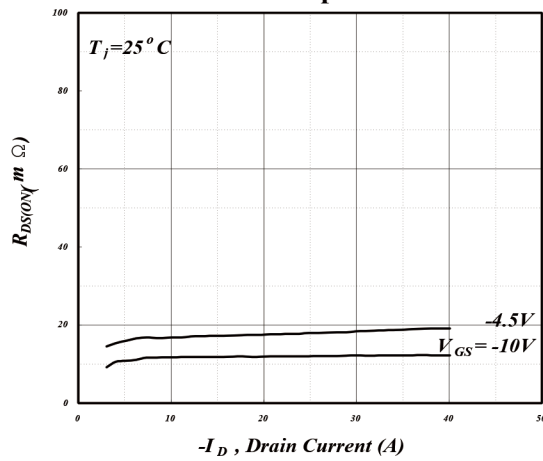
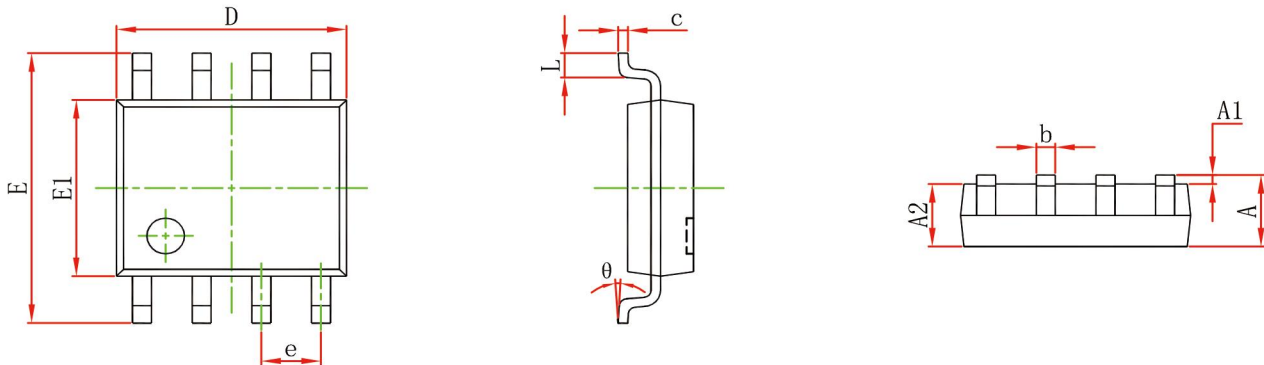
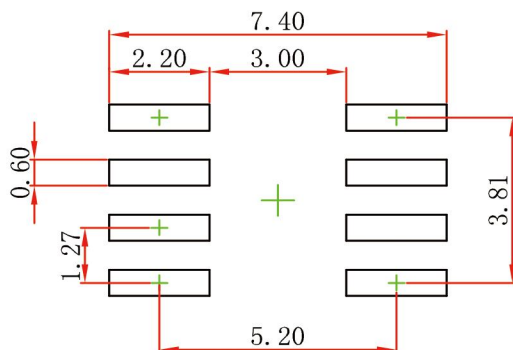


Fig 15. Typ. Drain-Source on State Resistance

SOP-8 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.800	5.000	0.189	0.197
e	1.270 (BSC)		0.050 (BSC)	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.